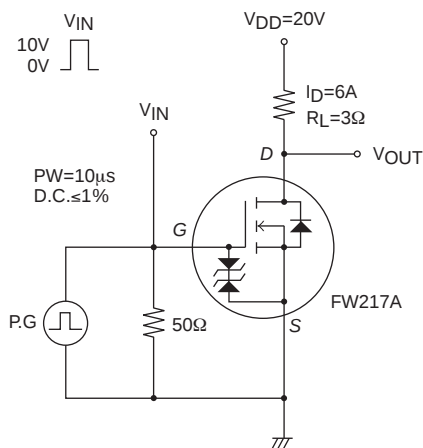


FW217A

Electrical Characteristics at Ta=25°C

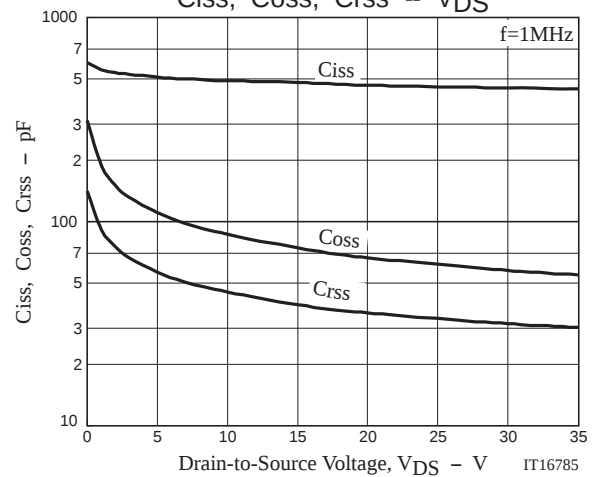
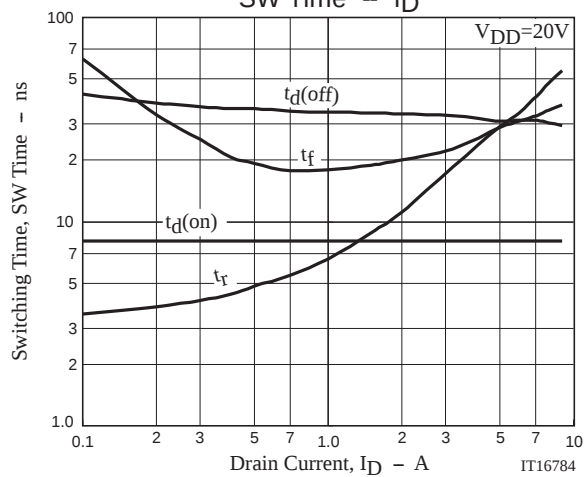
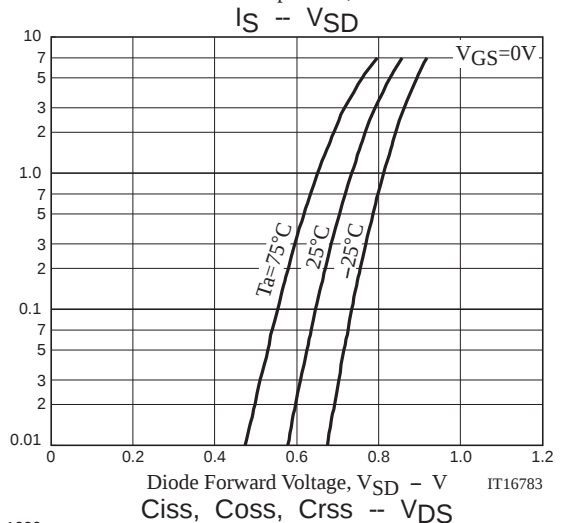
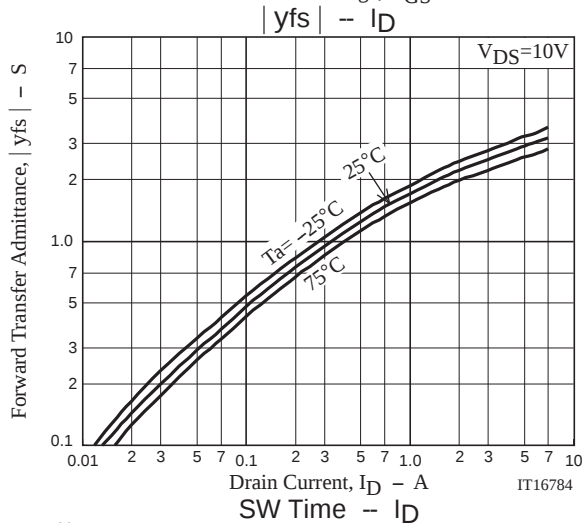
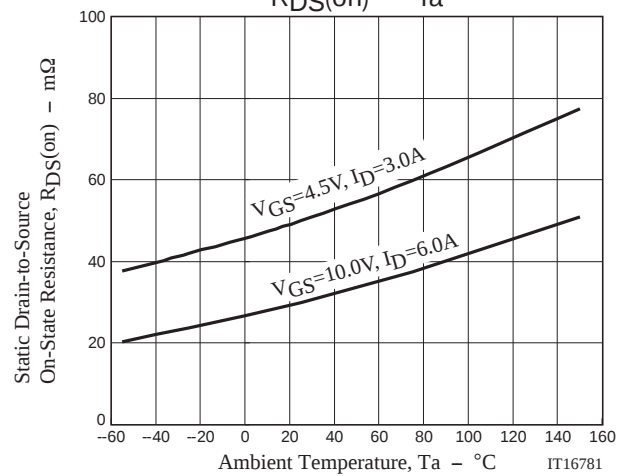
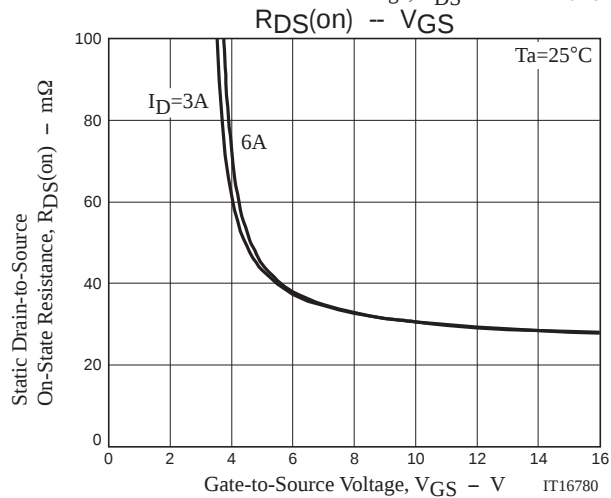
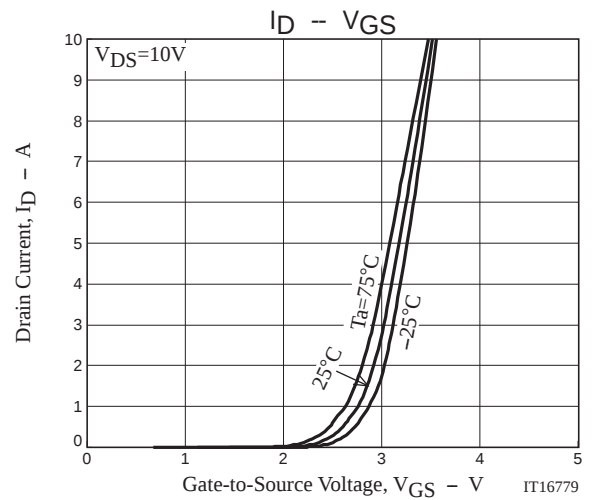
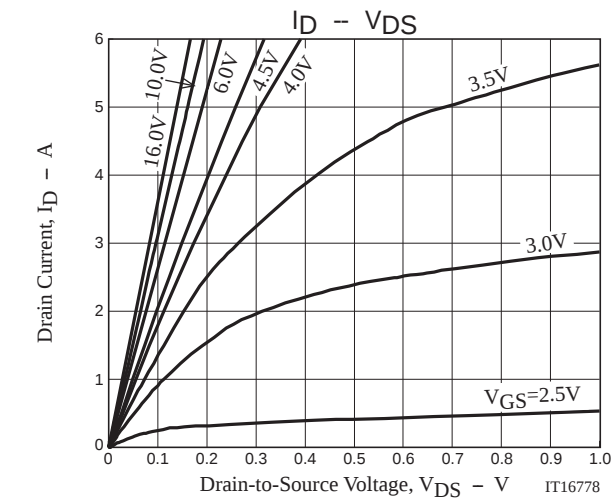
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	35			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=35V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.7		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=6A$		3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=6A, V_{GS}=10V$		30	39	$m\Omega$
	$R_{DS(on)2}$	$I_D=3A, V_{GS}=4.5V$		50	70	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		470		pF
Output Capacitance	C_{oss}			70		pF
Reverse Transfer Capacitance	C_{rss}			35		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		8		ns
Rise Time	t_r			34		ns
Turn-OFF Delay Time	$t_{d(off)}$			31		ns
Fall Time	t_f			30		ns
Total Gate Charge	Q_g	$V_{DS}=20V, V_{GS}=10V, I_D=6A$		10		nC
Gate-to-Source Charge	Q_{gs}			2		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$		0.84	1.2	V

Switching Time Test Circuit



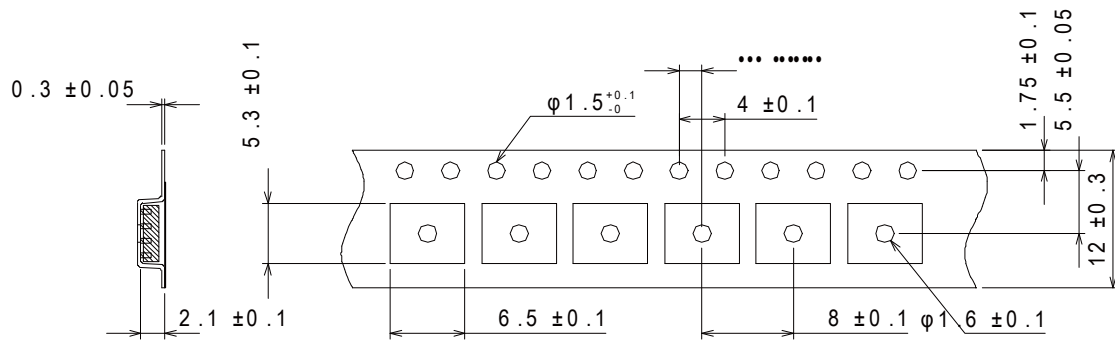
Ordering Information

Device	Package	Shipping	memo
FW217A-TL-2W	SOIC8	2,500pcs./reel	Pb Free and Halogen Free

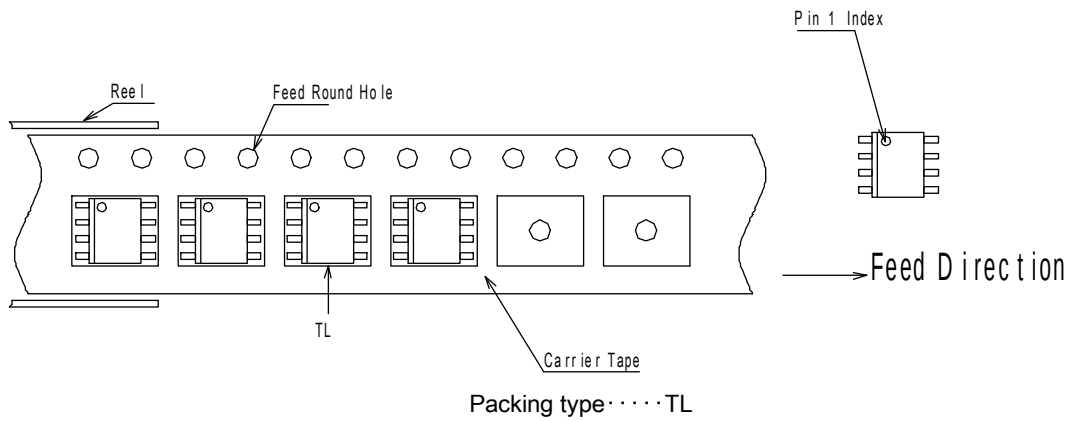


2. Taping configuration

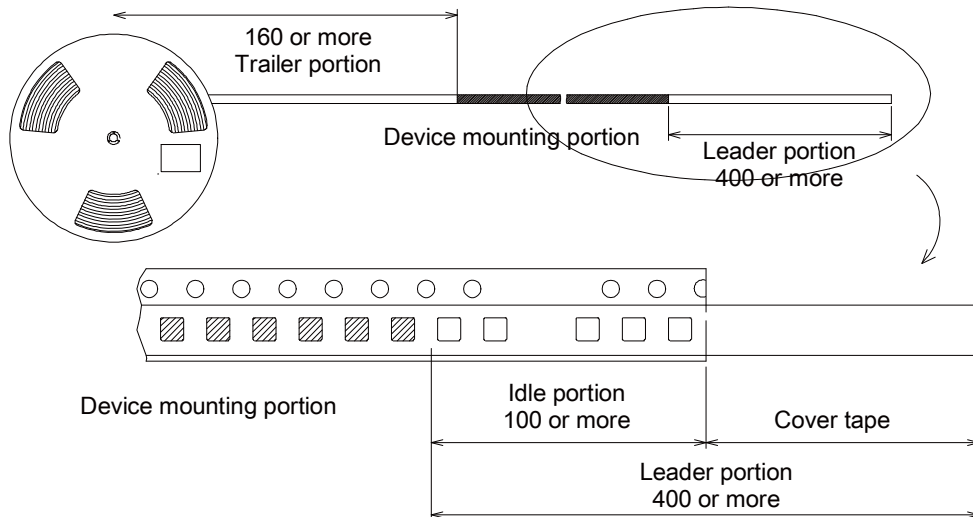
2-1. Carrier tape size (unit: mm)



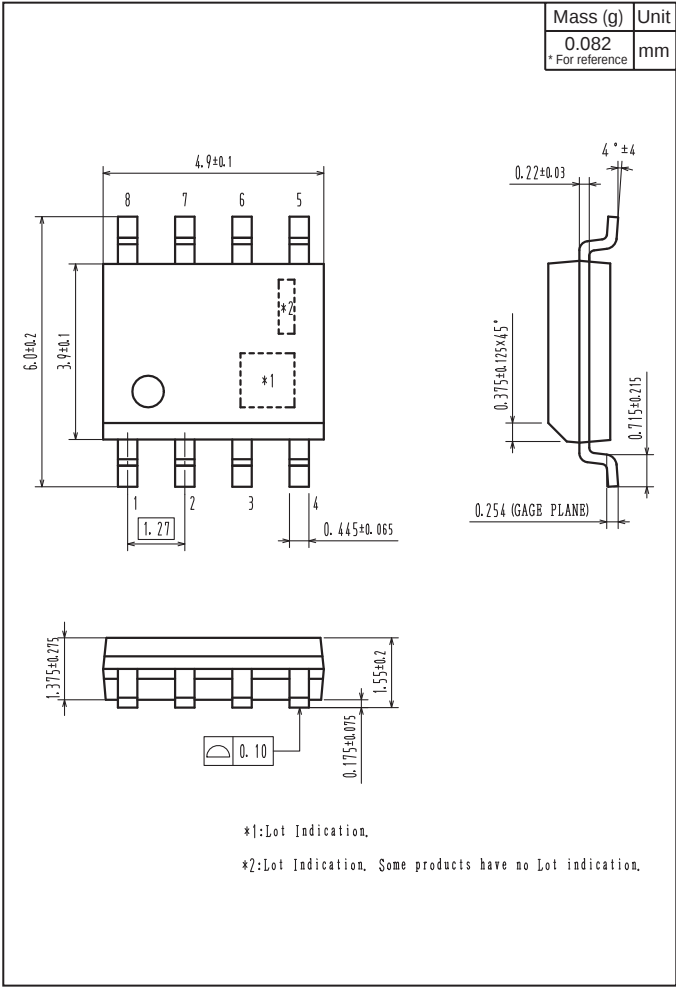
2-2. Device placement direction



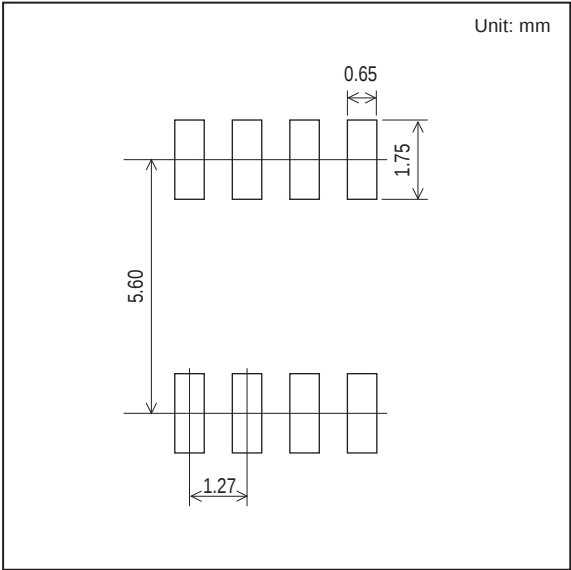
2-3. Leader portion and trailer portion (unit: mm)



Outline Drawing
FW217A-TL-2W



Land Pattern Example



Note on usage : Since the FW217A is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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